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[1]Universiti Teknologi, Malaysia;[2]Kyushu University, Japan;[3]Imperial College London, United Kingdom;[4]Xi'an Jiaotong Liverpool University, China

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Annealing Technology

(Room 102, 1st floor, East Auxiliary Building Affiliated to Guanghua Building)

Co-Chairs: Paul J. Timans, Mattson Thermal Products GmbH, Germany
S. Boninelli, IMM-CNR, Italy

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Junction and Contact Technologies for Compound Semiconductors

(Room 102, 1st floor, East Auxiliary Building Affiliated to Guanghua Building)

Co-Chairs: Hongyu Yu, Southern University of Science and Technology, China
Philippe Rodriguez, Univ. Grenoble Alpes, France

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(Invited)	[1] Tyndall National Institute, Ireland; [2] University College Cork, Ireland. [3] Trinity College Dublin, Ireland.	
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(Invited)	[a] Institute of Microelectronics, Chinese Academy of Sciences, China; [b]University of Chinese Academy of Sciences (UCAS), China	
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